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最新トランジスタ規格表 (New Transistor Manual) lists all the transistors registered with the Electronic Industries Association of Japan (EIAJ), arranged in a manner easy to look up. We hope that you will make full use of the data provided in this manual by referring to the Japanese-English translation key given below.

型名	社名	用途	構造	最大定格 ($T_c=25^\circ\text{C}$)					電 気 的 特 性 ($T_c=25^\circ\text{C}$)										外 形	備 考	
				V_{ce0} (V)	V_{be0} (V)	I_c (mA)	P_c (mW)	T_c ($^\circ\text{C}$)	I_{c0} 最大値 (μA)	直流又はパルス h_{FE}		バイアス		h_{FE}	h_{ie} h_{ie}^* (Ω)	h_{re} h_{re}^* ($\times 10^{-4}$)	h_{oe} h_{oe}^* (μS)	$f_{\alpha b}$ $f_{\alpha b}^*$ (Mc)			C_{ob} (pF)
1	2	3	4	5					6		7		8				9	10		11	12

- 1 TYPE NUMBER
- 2 ORIGINAL MANUFACTURER
- 3 USES
- 4 MATERIAL AND STRUCTURE
- 5 MAXIMUM RATINGS
- 6 I_{CBO} MAXIMUM VALUE AND V_{CB} VALUE (CRITERIA FOR MEASURING I_{CBO})
- 7 STANDARD VALUE OF DC/PULSE h_{FE} AND V_{CE} , I_C (CRITERIA FOR MEASURING DC/PULSE h_{FE})
- 8 STANDARD VALUE OF h PARAMETERS AND BIAS V_{CB} , I_E (CRITERIA FOR MEASURING h PARAMETERS)

- * INDICATES VALUE IN GROUNDED-BASE OPERATION, OTHERWISE VALUE IN EMITTER-GROUNDED OPERATION.
- 9 $f_{\alpha b}$ OF RF CHARACTERISTIC, EXCEPT IN CASE OF * WHICH INDICATES VALUE OF f_T .
- 10 C_{ob} AND $r_{bb'}$ OF RF CHARACTERISTICS EXCEPT IN CASE OF * IN $r_{bb'}$ COLUMN WHICH INDICATES VALUE OF h_{ie} (real)
- 11 OUTLINE
- 12 REMARKS

: とコンプリ : COMPLEMENTARY TO

型名	社名	用途	構造	最大定格 (T _a = 25°C)					電 氣 的 特 性 (T _a = 25°C)											外形	備考					
				V _{CBO} (V)	V _{EBO} (V)	I _C (mA)	P _C (mW)	T _J (°C)	I _{CBO} 最大値 (μA)	V _{CB} (V)	直流又はパルス h _{FE} V _{CE} (V) I _C (mA)	バイアス V _{CB} (V) I _E (mA)	h _{FE} h _{fs} *	h _{ie} h _{ih} * (Ω)	h _{re} h _{rb} (×10 ⁻⁴)	h _{oe} h _{ob} * (μΩ)	f _{αβ} f _T * (Mc)	C _{ob} (pF)	τ _{ββ} h _{ie(real)} * (Ω)							
★ 2SD124	日立	SW	Si. DJ	60	10	6 A	60 W (T _c =25°C)	175	25	30	30	4	1.5A	12	-50	t _{on} =1.6μS, t _f =5μS t _{off} =2.2μS	>0.5							102		
★ " 124A	"	"	"	75	10	7 A	60 W (T _c =25°C)	175	25	30	40	4	1.5A	4	-1A	t _{on} =1.6μS, t _f =5μS t _{off} =2.2μS	1							102		
★ " 125	"	"	"	100	10	6 A	60 W (T _c =25°C)	175	25	30	40	4	1.5A	12	-50		>0.5							102		
★ " 125A	"	"	"	100	10	7 A	60 W (T _c =25°C)	175	25	30	40	4	1.5A	4	-1A	t _{on} =1.6μS, t _f =5.5μS t _{off} =2.2μS	1							102		
★ " 126	"	PA. SW	Si. DJ	150	5	7 A	60 W (T _c =25°C)	175	25	30	10	4	6 A	4	-1A	t _{on} =1.6μS, t _f =6μS t _{off} =2.2μS								102		
★ " 127	ソニー	PA	Ge. A	23		500	250	85	15	15	82	1	20	6	-1		28*	2.5*	0.4*	4				12A		
★ " 127A	"	"	"	23		500	250	85	15	15	82	1	20	6	-1		28*	2.5*	0.4*	4				12A		
★ " 128	"	"	"	32		500	250	85	15	15	82	1	20	6	-1		28*	2.5*	0.4*	4				12A		
★ " 128A	"	"	"	32		500	250	85	15	15	82	1	20	6	-1		28*	2.5*	0.4*	4				12A		
★ " 129	東芝	"	Si. DJ	90	10	3 A	25 W (T _c =25°C)	150	1mA	50	30-200	5	500	10	-500					1*	250			99		
★ " 130	"	"	"	60	10	3 A	25 W (T _c =25°C)	150	1mA	50	30-200	5	500	10	-500					1*	250			99		
★ " 131	"	"	Si. T	100	5	5 A	50 W (T _c =25°C)	150	100	50	60	5	1 A												102	
★ " 132	日電	"	Si. EMe	100	6	20 A	150 W (T _c =25°C)	175	5mA	65	40	5	20 A												106	
★ " 133	"	"	"																							
★ " 134	ソニー	SW	Ge. A	60	3	5	30	65	8	15	40	5	3							2					18	
★ " 135	"	"	"																							
★ " 136	富士通	PA	Si. T	200	3	100	4 W (T _c =25°C)	150	10	150	80	10	50													98A
★ " 137	"	"	"	300	3	100	4 W (T _c =25°C)	150	10	150	80	10	50													98A
★ " 138	"	PA. SW	"	200	3	1 A	30 W (T _c =25°C)	175	20	150	75	10	0.5A													101
★ " 139	"	"	"	300	3	1 A	30 W (T _c =25°C)	175	20	150	75	10	0.5A													101
★ " 140	"	"	"																							
★ " 141	日電	PA	Si. E	20	5	3 A	15 W (T _c =25°C)	175	100	12	80	2	1 A													150
★ " 142	"	"	"	40	5	3 A	15 W (T _c =25°C)	175	100	20	80	2	1 A													150
★ " 143	"	"	"	80	5	2 A	15 W (T _c =25°C)	175	100	40	80	2	0.5A													150
★ " 144	"	"	"	100	5	2 A	15 W (T _c =25°C)	175	100	50	80	2	0.5A													150
★ " 145	"	"	"																							
★ " 146	富士通	PA. SW	Si. DJ	40	5	1 A	20 W (T _c =25°C)	175	20	30	60	4	500	6	-0.5A						1.4					101
★ " 147	"	"	"	60	5	1 A	20 W (T _c =25°C)	175	20	30	50	4	500	6	-0.5A						1.4					101
★ " 148	"	SW	"	70	5	2 A	20 W (T _c =25°C)	175	20	30	35	4	2 A	4	-100						1.2*					101
★ " 149	"	PA. SW	"	70	5	1 A	800	175	20	30	40	4	1 A	4	-100						1.2					84B